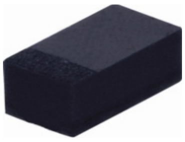
SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBUR0230L (RoHs Device)

I_O = 200 mA
V_R = 30 Volts



Features

Low forward voltage.

Designed for mounting on small surface.

Extremely thin / leadless package.

Majority carrier conduction.

Mechanical data

Case: 0603(1608) standard package, molded plastic.

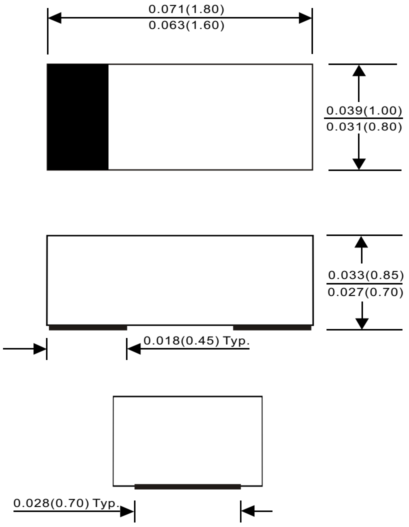
Terminals: Gold plated, solderable per MIL-STD-750,method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.003 gram(approx.).

0603(1608)



Dimensions in inches and (millimeter)

Maximum Rating (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V_{RRM}			35	V
Reverse voltage		V_R			30	V
Average forward current		I_O			200	mA
Forward current,surge peak	8.3ms single half sine-wave superimposed on rate load(JEDEC method)	I_{FSM}			1	A
Storage temperature		T_{STG}	-40		+125	°C
Junction temperature		T_j			+125	°C

Electrical Characteristics (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 200 mA	V_F			0.5	V
Reverse current	V_R = 10 V	I_R			30	uA

RATING AND CHARACTERISTIC CURVES (CDBUR0230L)

Fig. 1 - Forward characteristics

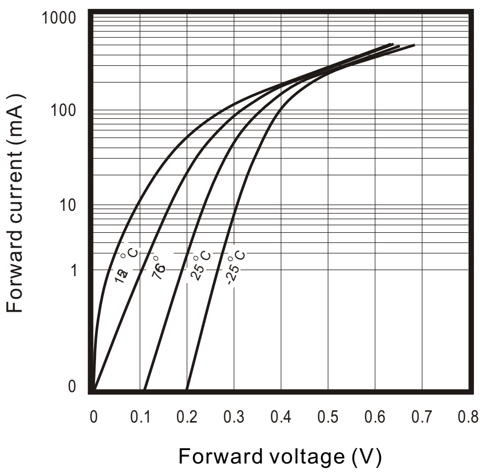


Fig. 2 - Reverse characteristics

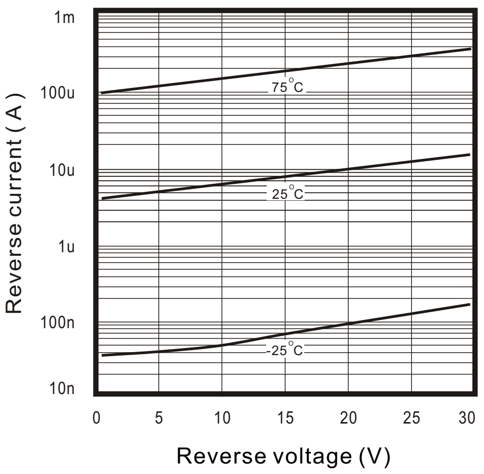


Fig.3 - Capacitance between terminals characteristics

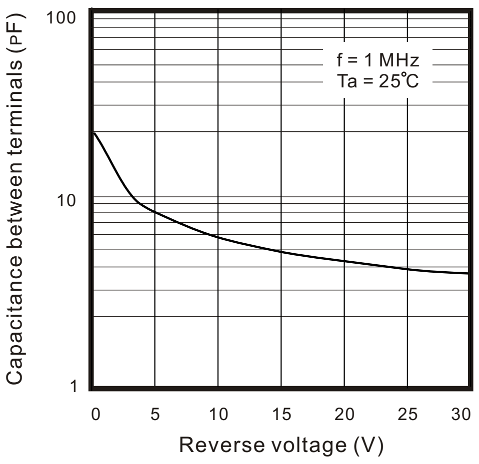


Fig.4 - Current derating curve